

AMENDMENTS TO THE SPECIFICATION

Please amend paragraph [0006], beginning on page 2, line 10, as follows:

[0006][0005] However, based on the physical characteristics of the flash memory, damage to the internal structure of the flash memory can easily occur after one million times of erasing steps. Accordingly, for extending the service life of the flash memory, the frequency of the erasing steps must be reduced. As described above, to write data, the flash memory has to locate a new block and erase the old one, in doing so, after one million erasure steps, the flash memory get easily damaged. Accordingly, finding a way to reduce the frequency of erasing steps of the flash memory for extending the service life thereof has become a priority in the field.

Please amend paragraph [0005], beginning on page 2, line 19, as follows:

[0005][0006] Accordingly, in the view of the foregoing, the present inventor makes a detailed study of related art to evaluate and consider, and uses years of accumulated experience in this field, and through several experiments, to create a method for reducing the frequency of erasing steps of the flash memory. The present invention provides an ~~innovated~~ innovative, cost effective a-method for reducing the frequency of erasing steps of the flash memory so that the service life of the flash memory can be substantially promoted.

Please amend paragraph [0009], as follows:

[0009] FIG. 1 is a flow chart (~~H~~) showing a conventional writing method.

Please amend paragraph [0010] as follows:

[0010] FIG. 2 is a flow chart (~~II~~) showing a conventional writing method.

Please amend paragraph [0011] as follows:

[0011] FIG. 3 is a flow chart (~~III~~) showing a conventional writing method.

Please amend paragraph [0012] as follows:

[0012] FIG. 4 is a flow chart (~~IV~~) showing a conventional writing method.

Please amend paragraph [0013] as follows:

[0013] FIG. 5 is a flow chart (~~V~~) showing a conventional writing method.

Please amend paragraph [0014] as follows:

[0014] FIG. 6 is a flow chart (~~VI~~) showing a conventional writing method.

Please amend paragraph [0015] as follows:

[0015] FIG. 7 is a flow chart (~~I~~) showing a writing method according to a preferred embodiment of the present invention.

Please amend paragraph [0016] as follows:

[0016] FIG. 8A is a flow chart (~~II~~) showing a writing method according to a preferred embodiment of the present invention.

Please amend paragraph [0017] as follows:

[0017] FIG. 8B is a flow chart (~~I~~) of a check area in the writing method according to a preferred embodiment of the present invention.

Please amend paragraph [0018] as follows:

[0018] FIG. 9A is a flow chart (~~II~~) showing a writing method according to a preferred embodiment of the present invention.

Please amend paragraph [0019] as follows:

[0019] FIG. 9B is a flow chart (~~II~~) of a check area in the writing method according to a preferred embodiment of the present invention.

Please amend paragraph [0020] as follows:

[0020] FIG. 10A is a flow chart (~~IV~~) showing a writing method according to a preferred embodiment of the present invention.

Please amend paragraph [0021] as follows:

[0021] FIG. 10B is a flow chart (~~III~~) of a check area in the writing method according to a preferred embodiment of the present invention.

Please amend paragraph [0024] as follows:

[0024] Referring to FIG. 7, a flow chart (I) shows a writing method according a preferred embodiment of the present invention. As shown, the host locates a new block and defines this new block as child block 2 and defines block A as mother block 1, and then writes into the page 3 and 4 of the block A in the logic page of the flash memory. Next, the host writes data into page 0 of child block 2 (shown in FIG. 8A). Meanwhile, the manager marks the first and the second byte in the redundant area ~~page~~ 21 of page 0 of child block 2 as C and H respectively to indicate that page 0 belongs to child block 2. The manager also marks the third byte in the redundant area 21 of page 0 as A x 03 to define that the page 0 of child block 2 is page 3 of mother block 1 for including a check area in page 0 (as shown in FIG. 8B). Furthermore, to write data into page 1 of child block 2 (shown in FIG. 9A), the manager marks the first and the second byte in the redundant area 22 of page 1 in child block as C and H to indicate that page 1 belongs to child block 2. The manager also to marks the third byte in the redundant area 22 of page 1 as A x 04 to define that the page 1 of child block 2 is page 4 of mother block 1 for including a check area in page 1 (as shown in FIG. 9B).

Please amend paragraph [0026] as follows:

[0026] Referring to FIGS. 10A and 10B, a flow chart (IV) of the writing method and a flow chart (III) of a check area in the writing method according a preferred embodiment of the present invention are respectively shown. As shown, when the manager writes data into page 3 in mother block 1 of the flash memory, the method of writing is similar to the above-mention procedure. In order to write data in an orderly manner into page 2 of child block 2, the manager marks the first and the second byte in the redundant page 23 of page 2 of child block 2 as C and

H to indicate that page 2 belongs to child block 2. The manager also marks the third byte in the redundant area 23 of page 2 as A x 03 to define that the page 2 of child block 2 is page 3 of mother block 1 for including a check area in page 2.